

**1. Scope :**

1-1. This specification applies to N channel depletion MOSFET chips,  
Device no. PM-0307

**2. Structure :**

- 2-1. Planar type.
- 2-2. Electrodes.  
Source : Aluminum alloy .  
Gate : Aluminum alloy .  
Drain : Gold alloy.

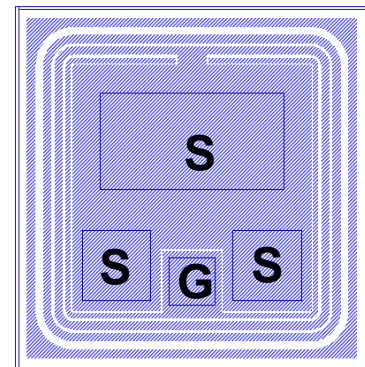
**3. Size :**

- 3-1. Chip size : 48 mils x48 mils (1.220 mm x1.220 mm ).
- 3-2. Chip thickness : 12 ±1.5mils ( 0.305± 0.038mm).
- 3-3. Pad size :  
Source : 25.1 mils x 12.8 mils (0.638 mm x 0.326mm ).  
Gate : 6.5 mils x 6.5 mils (0.164mm x 0.164 mm ).
- 3-4. Pattern drawing : Refer to the attached drawing.

**4. Absolute maximum rating (Ta = 25 °C)**

Parameter	Symbol	Rating	Unit
Continuous drain current V <sub>GS</sub> =0v	I <sub>D(m)</sub>	0.3	A
Drain-source Voltage	V <sub>DSS</sub>	400	V
Gate-source Voltage	V <sub>GS</sub>	±10	V
Operating junction and storage temperature range	T <sub>J</sub> T <sub>STG</sub>	-40to+150	°C

Pattern drawing



**5. Electrical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain to source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = -5V I <sub>D</sub> = 100uA	400			V
Gate to source off voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 25V I <sub>DS</sub> = 10uA	-1.8	-2.3	-3.5	V
Gate to source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±10V V <sub>DS</sub> = 0V		± 0.07	± 1	μA
Drain to source leakage current	I <sub>D(OFF)</sub>	V <sub>GS</sub> = -5V V <sub>DS</sub> = 400V			1	μA
Drain to source on resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 0V I <sub>D</sub> = 120mA		14	25	Ω
Diode forward voltage drop	V <sub>SD</sub>	V <sub>GS</sub> = -10V I <sub>SD</sub> = 120mA		0.84	1.8	V

